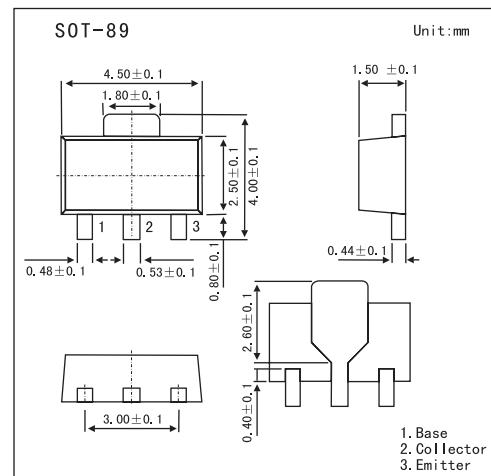


## High-Current Switching Applications

### 2SB1123

#### ■ Features

- Adoption of FBET, MBIT processes.
- Low collector-to-emitter saturation voltage.
- Large current capacity and wide ASO.
- Fast switching speed.



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-60	V
Collector-emitter voltage	V <sub>CBO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-6	V
Collector current	I <sub>C</sub>	-2	A
Collector current (pulse)	I <sub>CP</sub>	-4	A
Collector dissipation	P <sub>C</sub>	0.5	W
Mounted on a ceramic board (250mm×250.8mm)		1.3	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

**2SB1123**■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -50\text{V}$ , $I_E = 0$			-100	nA
Emitter-base cutoff current	$I_{EBO}$	$V_{EB} = -4\text{ V}$ , $I_C = 0$			-100	nA
DC current Gain	$h_{FE}$	$V_{CE} = -2\text{V}$ , $I_C = -100\text{mA}$	100		560	
Gain bandwidth product	$f_T$	$V_{CE} = -10\text{V}$ , $I_C = -50\text{mA}$		150		MHz
Output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}$ , $f = 1\text{MHz}$		22		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1\text{A}$ , $I_B = -50\text{mA}$		-0.3	-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1\text{A}$ , $I_B = -50\text{mA}$		-0.9	-1.2	V
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}$ , $I_E = 0$	-60			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$ , $R_{BE} = \infty$	-50			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$ , $I_C = 0$	-6			V
Turn-ON Time	$t_{on}$	<p><math>10I_B1=10I_B2=I_C=500\text{mA}</math> (For PNP, the polarity is reversed)</p>		60		ns
Storage Time	$t_{stg}$			450		ns
Fall Time	$t_f$			30		ns

## ■ hFE Classification

Marking	BF				
	Rank	R	S	T	
hFE		100~200	140~280	200~400	280~560